



TSB58T100S(A)S-255A

3A/100V⁽¹⁾, low VF Schottky barrier diode with trench MOS structure

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1473 μm	58 mil
	Top Metal Pad Size (B)	1379μm	54mil
	Chip Size (C)	1393μm	55mil
	Wafer Thickness (D)	255μm	9.5 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	TSB58T100AS-255A	Al/Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

Electrical Characteristics (T_J=25°C, unless otherwise specified)⁽²⁾

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	105	116	-	V	I _R =100μA
V _F	Instantaneous Forward Voltage	-	0.59	0.64	V	I _F =3A ⁽³⁾
		-	0.68	0.72	V	I _F =5A ⁽³⁾
I _R	Reverse Leakage Current	-	5	40	μA	V _R =105V
T _J , T _{STG}	Operating and Storage Temperature	-40°C to 150°C Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in DO-201packages. Actual performance may degrade when assembled.

YJ does not guarantee device performance after assembly;

(3) Pulse Width tp = < 300μS, Duty Cycle <2%;